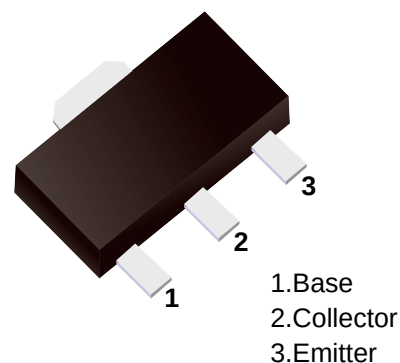


2SB772

■ PNP Transistors

■ Features

- PNP transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SD882



■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	-40	V
Collector to Emitter Voltage	V _{CE0}	-30	V
Emitter to Base Voltage	V _{EB0}	-6	V
Collector Current to Continuous	I _c	-3	A
Collector Dissipation	P _c	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

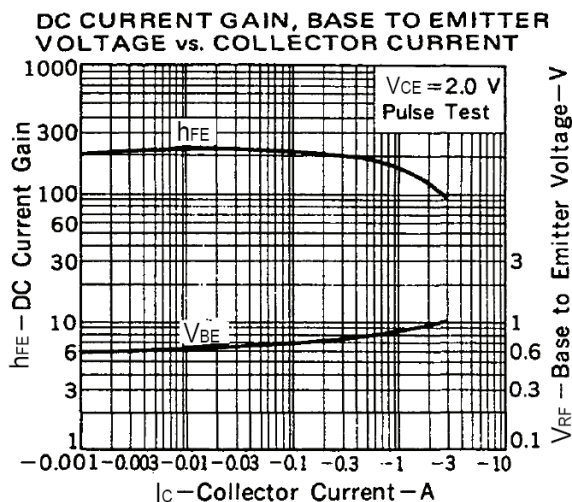
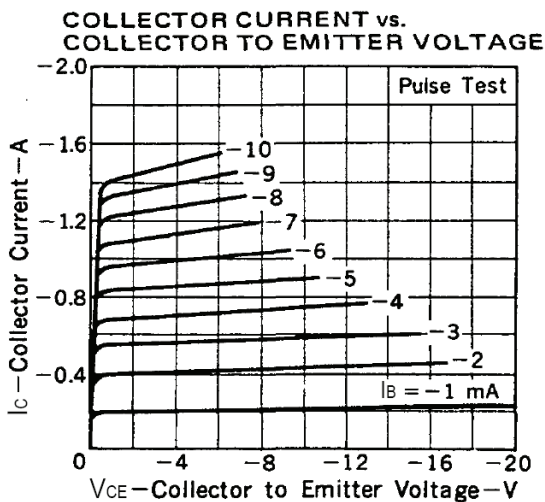
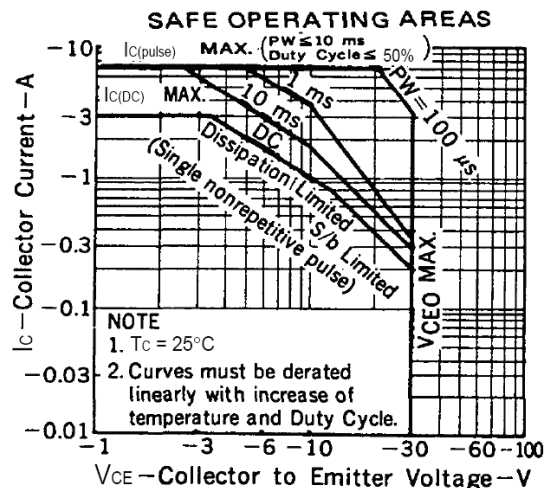
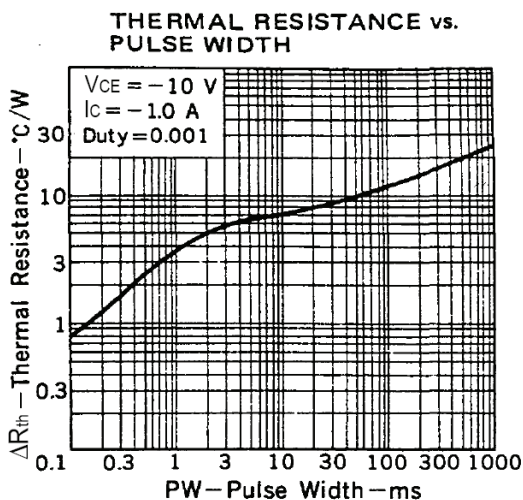
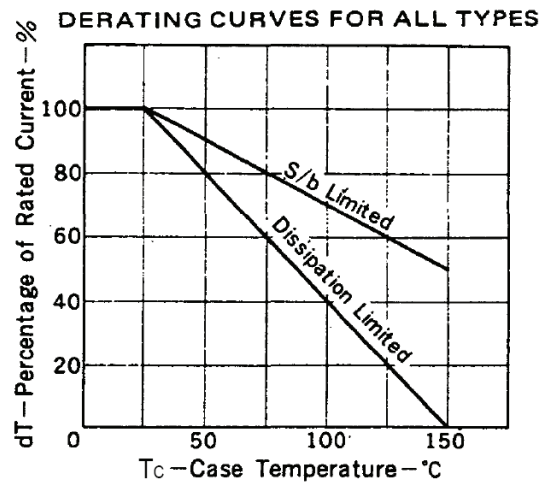
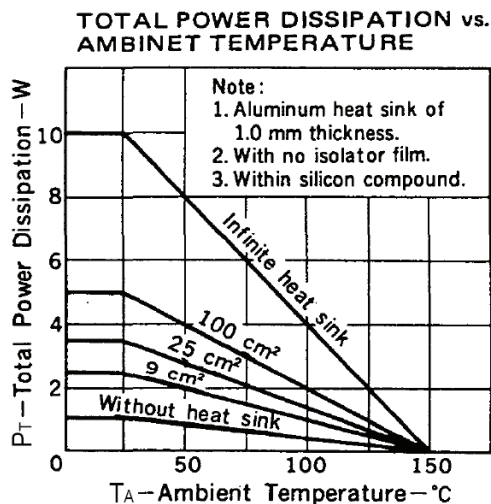
■ Electrical Characteristics Ta = 25°C

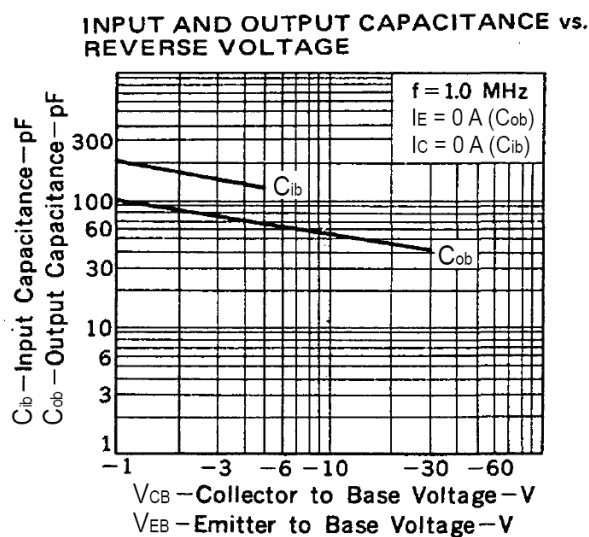
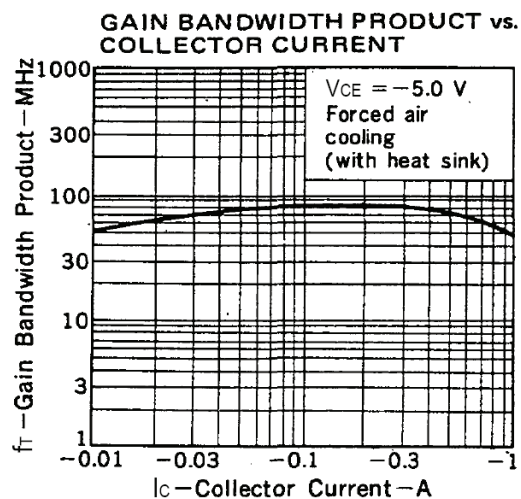
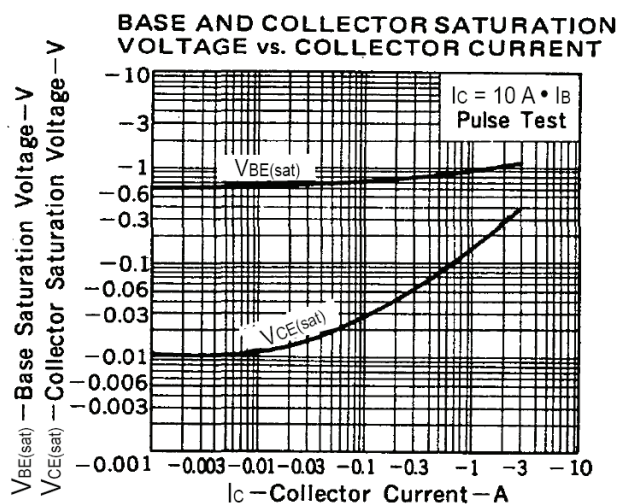
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =-100uA , I _E =0	-40			V
Collector-emitter breakdown voltage	V _{CE0}	I _c = -10 mA , I _B =0	-30			V
Emitter-base breakdown voltage	V _{EB0}	I _E = -100 uA , I _c =0	-6			V
Collector cut-off current	I _{CB0}	V _{CB} =-40 V , I _E =0			-1	μA
Emitter cut-off current	I _{EB0}	V _{EB} =-6V , I _c =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _c = -1A	60		400	
		V _{CE} =-2V, I _c = -100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-2A, I _B =- 0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =-2A, I _B = -0.2A			-1.5	V
Transition frequency	f _T	V _{CE} =-5 V, I _c =-0.1mA, f = 10MHz	50			MHz

■ Classification of h_{FE}(1)

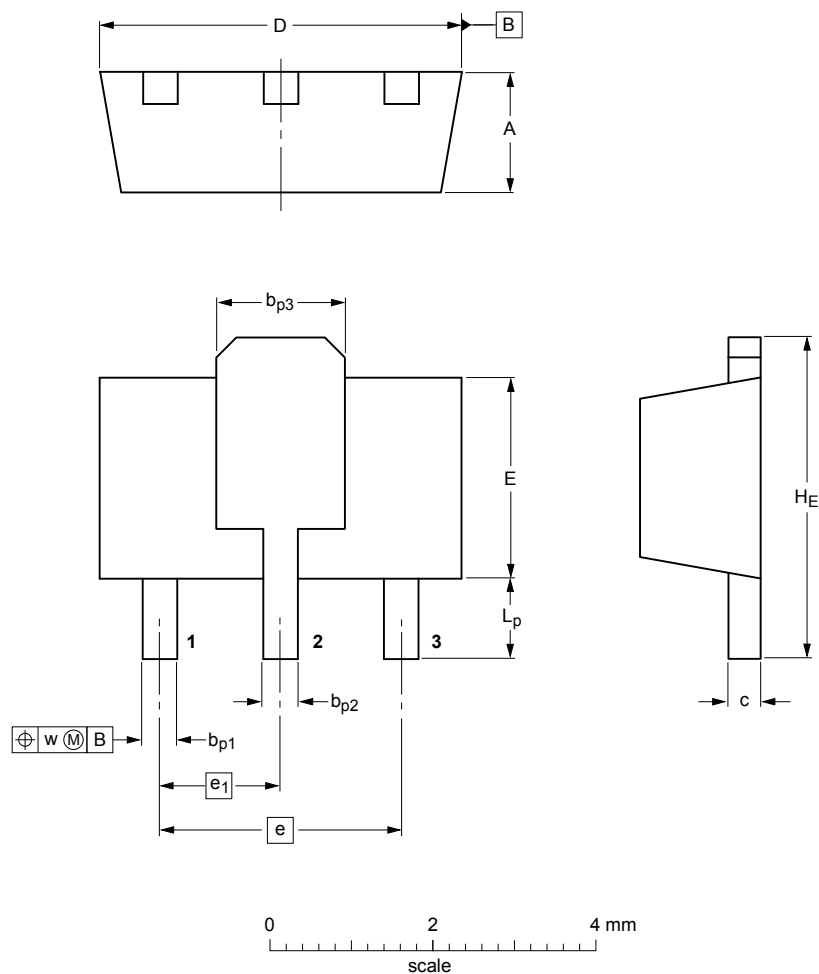
Type	2SB772-R	2SB772-Q	2SB772-P	2SB772-E
Range	60-120	100-200	160-320	200-400
Marking	772R	772Q	772P	772E

■ Typical Characteristics





■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13